



# SSL5257TE

Mains dimmable buck-boost LED driver IC 10 Ohm/700 V

Rev. 2 — 11 September 2015

Product data sheet

## 1. General description

The SSL5257TE is a highly integrated, high-precision buck-boost controller with an internal MOSFET. It is intended to drive low-cost compact dimmable LED lamps up to 10 W. The SSL5257TE is designed to achieve high power factor, phase-dimmable applications.

The SSL5257TE operates in Boundary Conduction Mode (BCM) with on-time control. It regulates a constant output current over line and load variations. The wide switching frequency range makes it possible to choose an inductor, which enables the optimization of inductor size, efficiency and EMI.

The SSL5257TE can start up and operate in switching mode directly from the rectified mains. To provide a low-cost driver design, an off-the-shelf inductor can be used, which provides flexibility in application design.



## 2. Features and benefits

- Integrated MOSFET (10 Ω/700 V)
- Supports most available dimming solutions
- Deep dimming level
- Flicker-free dimming
- Low component count ensuring a compact solution and small, single layer Printed-Circuit Board (PCB) footprint
- Excellent line regulation and load regulation and good LED output current accuracy
- Hotaru current control
- Internal thermal foldback
- Efficient BCM operation with:
  - ◆ Minimal recovery losses in freewheel diode
  - ◆ Zero Current Switching (ZCS) and Valley switching for turn-on of switch
  - ◆ Minimal inductance value and size required
  - ◆ High efficiency (up to 90 %)
  - ◆ Ultra low IC current during operation (< 200 μA)
- Auto-recovery protections:
  - ◆ UnderVoltage LockOut (UVLO)
  - ◆ Cycle-by-cycle OverCurrent Protection (OCP)
  - ◆ Internal OverTemperature Protection (OTP)
  - ◆ Output OverVoltage Protection (OVP)
  - ◆ Output Short Protection (OSP)
- Extended IC lifetime

## 3. Applications

- The SSL5257TE is intended for low-cost, non-isolated dimmable lighting applications that work from single mains voltage.

## 4. Quick reference data

**Table 1. Quick reference data**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>CC</sub>	supply voltage	operating range	[1] 9.9	-	16	V
R <sub>DSON</sub>	on-state resistance	I <sub>I(DRAIN)</sub> = 200 mA				
		T <sub>j</sub> = 25 °C	-	11.6	-	Ω
		T <sub>j</sub> = 125 °C	-	17.8	-	Ω
I <sub>I(DRAIN)</sub>	input current on pin DRAIN	duty cycle = 25 %	-0.8	-	+0.8	A
V <sub>I(DRAIN)</sub>	input voltage on pin DRAIN		-0.4	-	+700	V
V <sub>IO(COMP)</sub>	input/output voltage on pin COMP	operating range in application	2	-	4	V
V <sub>I(ISNS)</sub>	input voltage on pin ISNS	operating range in application	0	-	1.2	V
V <sub>I(DIM)</sub>	input voltage on pin DIM	operating range in application	0	-	2	V

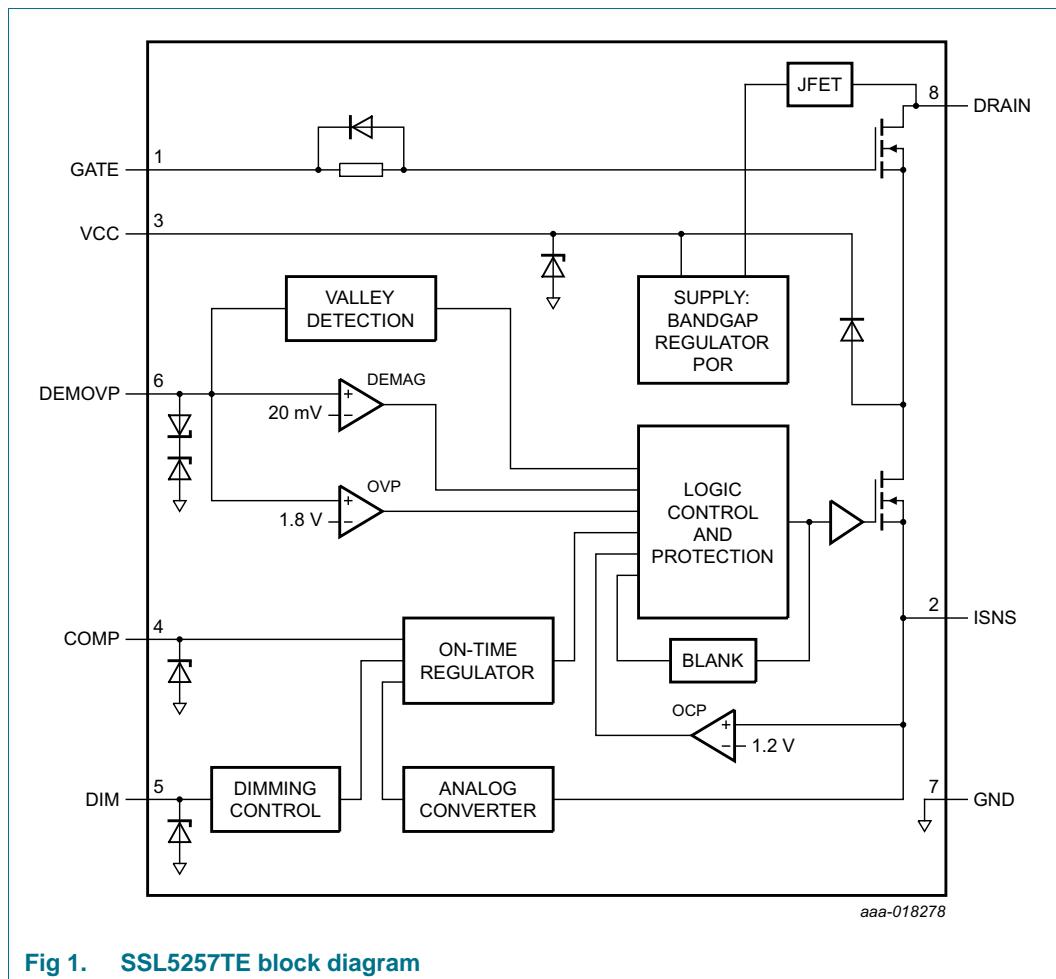
[1] An internal clamp sets the supply voltage. The current into the VCC pin must not exceed the maximum I<sub>VCC</sub> value (see [Table 4](#)).

## 5. Ordering information

**Table 2. Ordering information**

Type number	Package		
	Name	Description	Version
SSL5257TE	HSO8	plastic thermal enhanced small outline package; 8 leads; body width 3.9 mm; exposed die pad	SOT786-3

## 6. Block diagram



## 7. Pinning information

### 7.1 Pinning

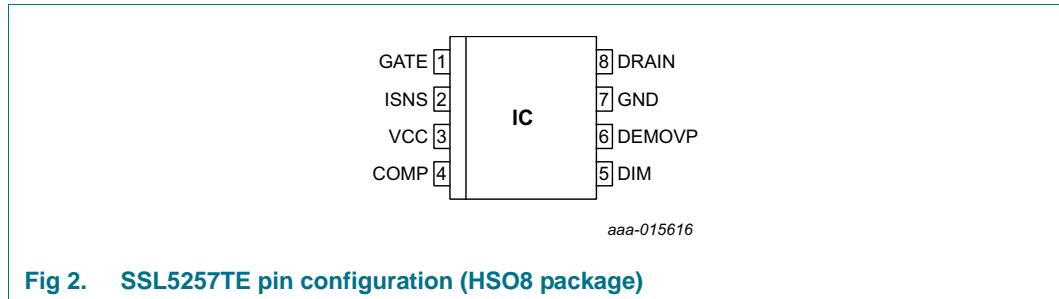


Fig 2. SSL5257TE pin configuration (HSO8 package)

### 7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
GATE	1	gate of internal switch
ISNS	2	ground current sense input
VCC	3	supply voltage
COMP	4	loop compensation to provide stable response
DIM	5	dimming control input
DEMOVP	6	input from LED output for demagnetization timing, valley detection, and OVP
GND	7	ground
DRAIN	8	drain of high-side internal MOSFET

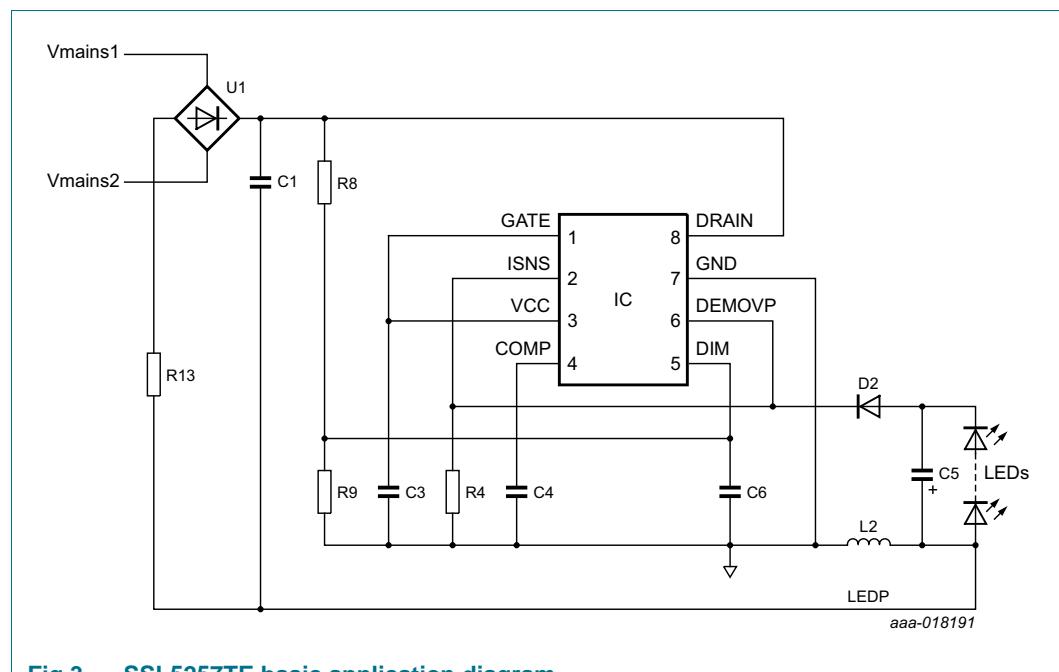
## 8. Functional description

## 8.1 Converter operation

The SSL5257TE is a high-side switching on-time controlled BCM buck-boost converter. [Figure 3](#) shows the basic application diagram. To save IC supply current, an integrated source-switch topology is used.

The converter operates at the boundary between Continuous Conduction Mode (CCM) and Discontinuous Conduction Mode (DCM). Figure 5 shows the waveforms.

When the internal switch is switched on at  $t_0$ , the inductor current  $I_L$  proportionally to  $V_{in}$  builds up from zero during the source-switch on-time ( $t_0$  to  $t_1$ ). Energy is stored in inductor L2. When the internal source-switch switches off at  $t_1$ ,  $I_L$  flows through the freewheeling diode D2 and the output capacitor C5. The inductor current drops proportionally to  $V_{out}$  ( $t_2$  to  $t_3$ ). When  $I_L$  reaches zero at  $t_3$ , a new switching cycle is started after a short delay ( $t_3$  to  $t_{00}$ ) from valley detection.



**Fig 3. SSL5257TE basic application diagram**

## 8.2 On-time control

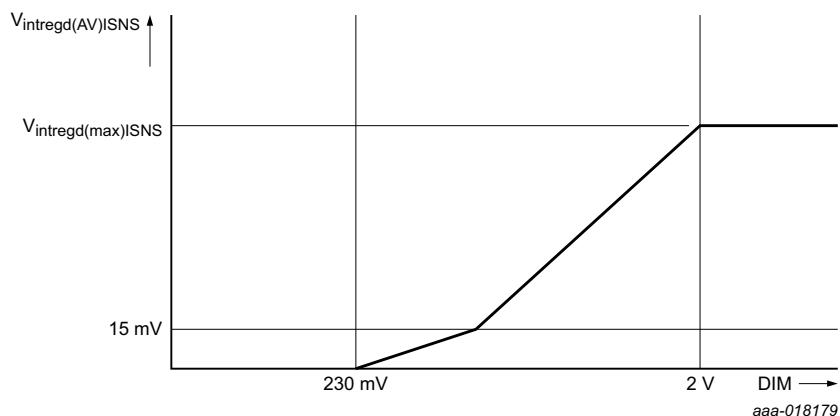
When measuring the inductor current  $I_L$  using sense resistor R4, the on-time is regulated so that the average ISNS voltage ( $V_{intregd(AV)ISNS}$ ) is regulated to  $V_{intregd(max)ISNS}$  (155 mV typical) during the off-time of the main switch. The average output current  $I_{out}$  can be calculated with [Equation 1](#):

$$I_{out} = \frac{V_{intregd(AV)ISNS}}{R4} \quad (1)$$

### 8.3 Dimming control

When measuring the phase-cut mains voltage using the DIM pin, the DIM voltage modulates the internal reference voltage. The dimmed output current  $I_{O(dim)}$  can be calculated with [Equation 2](#):

$$I_{O(dim)} = \frac{V_{intregd(AV)ISNS}}{R4} \quad (2)$$



**Fig 4. Dimming control transfer function**

## 8.4 Valley detection

When  $I_L$  has decreased to zero at  $t_3$ , the LEDP voltage starts to oscillate around the IC ground, with amplitude  $V_{out}$  and frequency ( $f_{ring}$ ). A special circuit called valley detection is integrated in the SSL5257TE. It senses when the LEDP voltage reaches its lowest level (valley) at the DEMOVP pin. The internal source-switch is switched on again when the valley is detected. As a result, the switch-on switching losses are reduced.

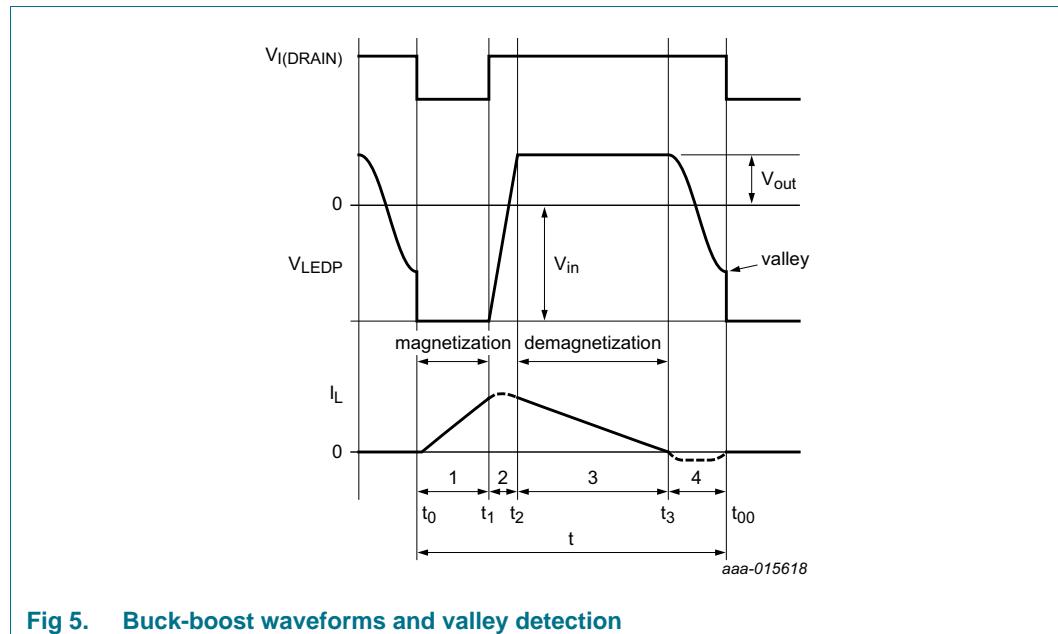


Fig 5. Buck-boost waveforms and valley detection

## 8.5 High-voltage start-up and supply

Before start-up, the capacitor on the VCC pin is charged with an internal current source  $I_{ch}$  (1 mA typical) from the high-voltage mains using the DRAIN pin. When the start-up voltage ( $V_{startup}$ ) is reached, the internal current source is switched off. The SSL5257TE starts switching. During normal operation, a linear regulator controls the VCC supply voltage to  $V_{reg}$  (13.6 V typical).

The linear regulator can supply a maximum current of  $I_{reg(max)}$  (3.5 mA typical) to the VCC pin. During deep dimming, the DRAIN voltage is low for the major part of the mains cycle. As the supply current of the IC is typically only 160  $\mu$ A, the linear regulator can keep  $V_{CC}$  in regulation at very small dimmer conduction angles.

When  $V_{CC}$  drops to below the undervoltage lockout threshold voltage ( $V_{th(UVLO)}$ ), switching is inhibited. Using the internal current source, a restart is attempted.

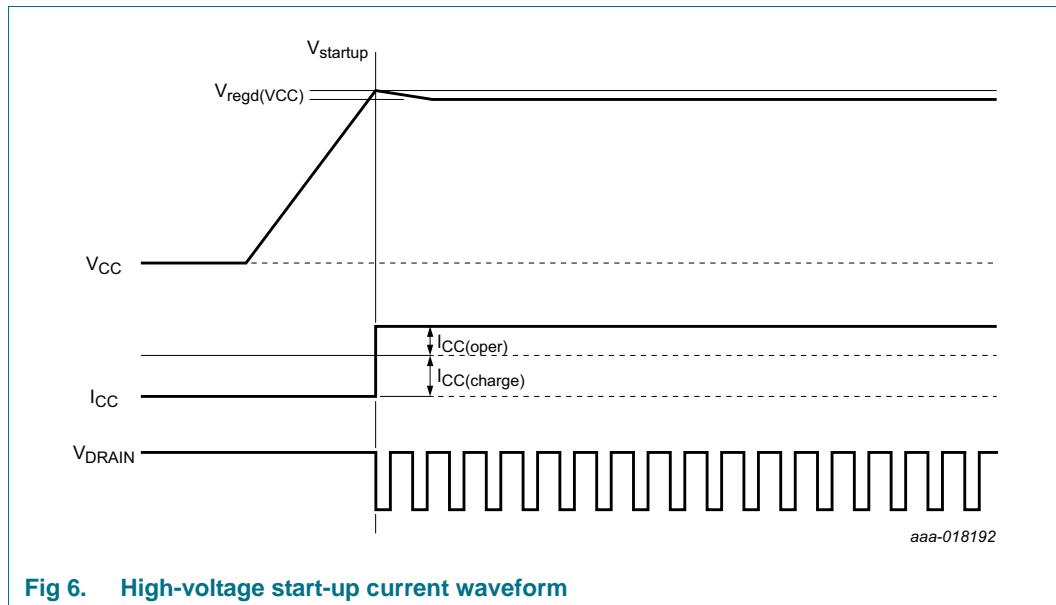


Fig 6. High-voltage start-up current waveform

## 8.6 Leading-Edge Blanking (LEB)

To prevent false detection of overcurrent, a blanking time following switch-on is implemented. When the internal switch turns on, a short current spike can occur because of the capacitive discharge of voltage over the drain and the source. It is disregarded during the LEB time ( $t_{leb}$ ).

## 8.7 Magnetization switching

When the mains voltage is very low, during dimming or around the zero crossings of the mains, the system hardly delivers any energy to the LED. To improve the efficiency, maximum off-time ( $t_{off(\max)}$ ) switching limits the switching frequency to < 25 kHz. A peak voltage on the ISNS pin below the  $V_{I(\min)\text{ISNS}}$  voltage indicates a low mains voltage.

## 8.8 Hotaru current

Before start-up, an  $I_{\text{sink}(\text{DRAIN})}$  current (10 mA typical) is drawn from the DRAIN pin. This current prevents that the converter reaches the start-up voltage when the attached dimmer has a leakage current. The capacitor across the dimmer that is typically present, e.g., or an indication light inside the dimmer can cause the dimmer leakage current.

When the start-up voltage is reached, the converter starts switching and the Hotaru current is switched off. When  $V_{CC}$  drops to below the undervoltage lockout threshold voltage ( $V_{th(\text{UVLO})}$ ), switching is inhibited. The Hotaru current is switched on again.

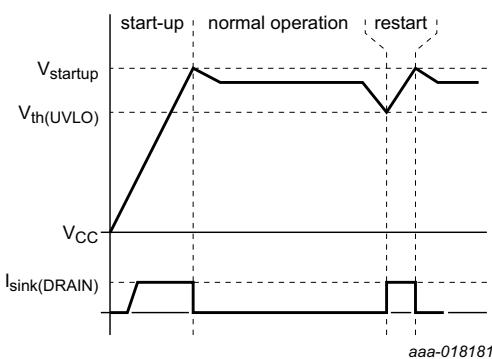


Fig 7. Hotaru current waveform

## 8.9 Thermal foldback

To limit the power dissipation in the IC and in the application when the IC junction temperature exceeds  $T_{fold}$  ( $135^{\circ}\text{C}$  typical), the SSL5257TE integrates a thermal foldback function. When the IC junction temperature exceeds  $T_{fold}$ , the LED output current  $I_{LED}$  decreases linearly with the junction temperature to 65 % of the maximum output current value, triggering the overtemperature protection.

Because the LED output current reduces when the foldback temperature ( $T_{fold}$ ) is reached, the total power dissipation in the application reduces and a further temperature increase is slowed down. Under high-ambient temperature conditions, the thermal foldback function limits the chance of the application reaching the overtemperature protection limit which results in a blinking LED.

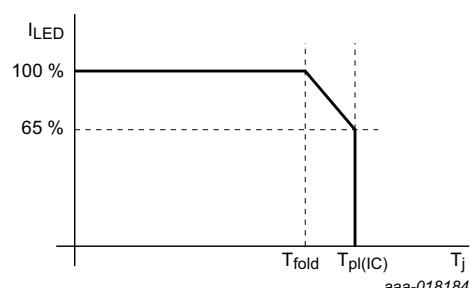


Fig 8. Thermal foldback waveform

## 8.10 Protections

The IC incorporates the following protections:

- UnderVoltage LockOut (UVLO)
- Cycle-by-cycle OverCurrent Protection (OCP)
- Internal OverTemperature Protection (OTP)
- Cycle-by-cycle maximum on-time protection
- Output OverVoltage Protection (OVP)
- Output Short Protection (OSP)

### 8.10.1 UnderVoltage LockOut (UVLO)

When the voltage on the VCC pin drops to below  $V_{th(UVLO)}$ , the IC stops switching. An attempt is made to restart IC when the  $V_{CC} > V_{startup}$ .

### 8.10.2 Cycle-by-cycle OverCurrent Protection (OCP)

The SSL5257TE contains a built-in peak current detector. It triggers when the voltage at the ISNS pin reaches the peak level  $V_{I(max)ISNS}$ . A resistor connected to the ISNS pin senses the current through the inductor  $I_L$ . The maximum current in inductor  $I_{L(max)}$  can be calculated with [Equation 3](#):

$$I_{L(max)} = \frac{V_{I(max)ISNS}}{R4 + R_{bond} \times \delta_{swon}} \quad (3)$$

Where:

- $R_{bond}$  is the ISNS bond wire resistance
- $\delta_{swon}$  is the switch-on duty cycle

The sense circuit is activated after the LEB time ( $t_{leb}$ ). It automatically provides protection for maximum LED current during operation. A propagation delay exists between overcurrent detection and the actual source-switch switch-off. Due to this delay, the actual peak current is slightly higher than the OCP level set by the resistor in series with the ISNS pin.

### 8.10.3 OverTemperature Protection (OTP)

When the internal OTP function is triggered at IC junction temperature  $T_{pl(IC)}$ , the converter stops switching. The IC resumes switching when the IC temperature drops to below  $T_{pl(IC)rst}$ .

### 8.10.4 Cycle-by-cycle maximum on-time protection

Measuring the inductor current  $I_L$  using sense resistor  $R_{sense}$  regulates the on-time. The on-time is limited to a fixed value ( $t_{on(max)}$ ). It protects the system and the IC when the ISNS pin is shorted or the system works at very low mains.

### 8.10.5 Output OverVoltage Protection (OVP)

Measuring the voltage at the DEMOVP pin during the secondary stroke gives an accurate output OVP. The resistive divider connected between the LEDP node and the DEMOVP pin sets the maximum LED voltage.

An internal counter prevents false OVP detection because of noise on the DEMOVP pin. After three continuous cycles with a DEMOVP pin voltage exceeding the OVP level, OVP is triggered.

OVP triggers a restart sequence:  $V_{CC}$  is discharged to below  $V_{rst(latch)}$ . When  $V_{rst(latch)}$  is reached, the system restarts.

### 8.10.6 Output Short Protection (OSP)

The converter operates in Discontinuous Conduction Mode (DCM). A new cycle is only started after the previous cycle has ended. Measuring the voltage on the DEMOVP pin detects the end of the cycle. When the DEMOVP pin voltage drops to below the demagnetization level ( $V_{det(demag)}$ ) and a valley is detected, a new cycle starts. The converter regulates the adjusted output current and the on-time is reduced to a safe value by this feedback. The reduced on-time in combination with a very long demagnetization period prevents the converter from any damage or excessive dissipation.

To prevent false demagnetization detection, a blanking time ( $t_{sup(xfmr\_ring)}$ ) is implemented at the start of the secondary stroke.

## 8.11 Supply management

The IC starts up when the voltage at the VCC pin exceeds  $V_{startup}$ . The IC locks out (stops switching) when the voltage at the VCC pin drops to below  $V_{th(UVLO)}$ . The hysteresis between the start and stop levels allows the VCC capacitor to supply the IC during zero-crossings of the mains.

The SSL5257TE incorporates an internal VCC clamping circuit. The clamp limits the voltage on the VCC supply pin to the maximum value  $V_{clamp(VCC)}$ .

## 9. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
<b>Voltages</b>					
V <sub>CC</sub>	supply voltage	current limited [1][2]	-0.4	18	V
V <sub>GATE</sub>	gate voltage	current limited [1][2]	-0.4	18	V
V <sub>I(DRAIN)</sub>	input voltage on pin DRAIN	current limited [1][2]	-0.4	+700	V
V <sub>I(ISNS)</sub>	input voltage on pin ISNS		-0.4	+5	V
V <sub>IO(COMP)</sub>	input/output voltage on pin COMP		-0.4	+5.3	V
V <sub>I(DEMOVP)</sub>	input voltage on pin DEMOVP		-6	+6	V
V <sub>I(DIM)</sub>	input voltage on pin DIM		-0.4	+5	V
<b>Currents</b>					
I <sub>I(VCC)</sub>	input current on pin VCC		-	+8.8	mA
I <sub>I(DRAIN)</sub>		RMS current; maximum average current = 100 mA; duty cycle < 25 %	-	210	mA
		duty cycle < 25 %	-0.8	+0.8	A
I <sub>I(ISNS)</sub>	input current on pin ISNS	duty cycle < 25 %	-0.8	+0.8	A
<b>General</b>					
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> < 75 °C	-	0.9	W
T <sub>stg</sub>	storage temperature		-55	+150	°C
T <sub>j</sub>	junction temperature		-40	+160	°C
<b>ESD</b>					
V <sub>ESD</sub>	electrostatic discharge voltage	class 1			
		human body [3]	-2000	+2000	V
		charged device [4]	-500	+500	V

[1] The current into the VCC pin must not exceed the maximum I<sub>VCC</sub> value.

[2] An internal clamp sets the supply voltage and current limits.

[3] Equivalent to discharge a 100 pF capacitor through a 1.5 kΩ series resistor.

[4] Charged device model: equivalent to charging the IC up to 1 kV and the subsequent discharging of each pin down to 0 V over a 1 Ω resistor.

## 10. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air; HSO8 package; PCB: 2 cm × 3 cm; 35 $\mu$ m copper (Cu)/layer; copper for IC: 6.6 cm	117	K/W
		in free air; HSO8 package; PCB: JEDEC 2s2p	49	K/W
$\Psi_{j-top}$	thermal characterization parameter from junction to top of package	top package temperature measured at the warmest point on top of the case; HSO8 package	4	K/W

## 11. Characteristics

**Table 6. Characteristics**

$T_{amb} = 25^\circ\text{C}$ ;  $V_{CC} = 15\text{ V}$ ; all voltages are measured with respect to ground pin (pin 7); currents are positive when flowing into the IC; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
<b>Supply (pin VCC)</b>							
$V_{startup}$	start-up voltage		13.5	13.95	14.35	V	
$V_{th(UVLO)}$	undervoltage lockout threshold voltage		9.7	10	10.3	V	
$V_{regd(VCC)}$	regulated voltage on pin VCC		13.2	13.65	14.1	V	
$V_{clamp(VCC)}$	clamp voltage on pin VCC	$I_{I(VCC)} = 2.6\text{ mA}$	[1]	14.8	15.2	15.8	V
$V_{rst(latch)}$	latched reset voltage		5.8	6.2	6.6	V	
$I_{CC(\text{oper})}$	operating supply current	switching at 100 kHz	160	180	200	$\mu\text{A}$	
$I_{CC(\text{ch})}$	charge supply current		-1.2	-1	-0.8	mA	
$I_{reg(\text{max})}$	maximum regulation current	$V_{CC} < V_{regu(VCC)}$	-4.5	-3.9	-3.3	mA	
<b>Loop compensation (pin COMP)</b>							
$V_{IO(COMP)}$	input/output voltage on pin COMP	operating range in application	2	-	4	V	
$V_{ton(zero)}$	zero on-time voltage		1.9	2.0	2.1	V	
$V_{ton(\text{max})}$	maximum on-time voltage		3.8	4.0	4.2	V	
$V_{clamp(COMP)}$	clamp voltage on pin COMP	$I_{I(COMP)} = 1\text{ mA}$	4.4	4.8	5.2	V	
$t_{on(\text{max})}$	maximum on-time	$V_{IO(COMP)} = 4\text{ V}$	11.5	14.5	17.5	$\mu\text{s}$	
$I_{O(COMP)}$	output current on pin COMP	$V_{I(\text{ISNS})} = 0\text{ V}; V_{I(\text{DIM})} > 2\text{ V}$	-3.6	-3.0	-2.4	$\mu\text{A}$	
$I_{dch(COMP)}$	Discharge current on pin COMP	$V_{I(\text{DIM})} = 0\text{ V}$	280	480	680	nA	
<b>Valley detection and overvoltage detection (pin DEMOVP)</b>							
$I_{prot(DEMOVP)}$	protection current on pin DEMOVP	open pin current; $V_{I(DEMOVP)} = 0\text{ V}$	-250	-180	-50	nA	
$V_{th(ovp)}$	overvoltage protection threshold voltage		1.75	1.82	1.89	V	

**Table 6. Characteristics ...continued**

$T_{amb} = 25^{\circ}\text{C}$ ;  $V_{CC} = 15\text{ V}$ ; all voltages are measured with respect to ground pin (pin 7); currents are positive when flowing into the IC; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$N_{cy(ovp)}$	number of overvoltage protection cycles		-	3	-	-
$(dV/dt)_{vrec}$	valley recognition voltage change with time	[2]	-	-3.8	-	$\text{V}/\mu\text{s}$
$V_{det(demag)}$	demagnetization detection voltage		6	20	34	$\text{mV}$
$t_{sup(xfmr\_ring)}$	transformer ringing suppression time		1.13	1.45	1.77	$\mu\text{s}$
<b>Current sensing (pin ISNS)</b>						
$V_{I(ISNS)}$	input voltage on pin ISNS	operating range in application	0	-	1.2	$\text{V}$
$V_{I(min)ISNS}$	minimum input voltage on pin ISNS		15	25	35	$\text{mV}$
$V_{I(max)ISNS}$	maximum input voltage on pin ISNS		1.1	1.2	1.3	$\text{V}$
$t_{on(min)}$	minimum on-time	[3]	280	380	480	$\text{ns}$
$t_d$	delay time	[3]	-	100	-	$\text{ns}$
$g_m(ISNS)$	ISNS transconductance	$V_{I(ISNS)}$ to $I_{O(COMP)}$	18	19.3	20.6	$\mu\text{A}/\text{V}$
$V_{intregd(max)ISNS}$	maximum internal regulated voltage on pin ISNS	$V_{I(DIM)} > 2\text{ V}$	0.150	0.155	0.160	$\text{V}$
<b>Dimming control (pin DIM)</b>						
$V_{I(DIM)}$	input voltage on pin DIM	operating range in application	0	-	2	$\text{V}$
$V_{intregd(AV)}/V_{dim}$	average internal regulated voltage ratio to dimming voltage	0.65 $\text{V} < V_{DIM} < 2\text{ V}$	95	100	105	$\text{mV}/\text{V}$
		0.25 $\text{V} < V_{DIM} < 0.6\text{ V}$	25	35	45	$\text{mV}/\text{V}$
$V_{clamp(DIM)}$	clamp voltage on pin DIM	$I_{I(DIM)} = 200\text{ }\mu\text{A}$	4.3	4.5	4.7	$\text{V}$
<b>Driver (pin DRAIN)</b>						
$R_{DSon}$	on-state resistance	$I_{I(DRAIN)} = 200\text{ mA}$				
		$T_j = 25^{\circ}\text{C}$	-	11.6	13	$\Omega$
		$T_j = 125^{\circ}\text{C}$	-	17.8	20[4]	$\Omega$
$t_{off(max)}$	maximum off-time		30	40	50	$\mu\text{s}$
$I_{leak(DRAIN)}$	leak current on pin DRAIN	$V_{I(DRAIN)} = 700\text{ V}$	-	-	10	$\mu\text{A}$
$I_{sink(DRAIN)}$	sink current on pin DRAIN	Hotaru current; $V_{CC} < V_{startup}$	8.5	10	11.5	$\text{mA}$

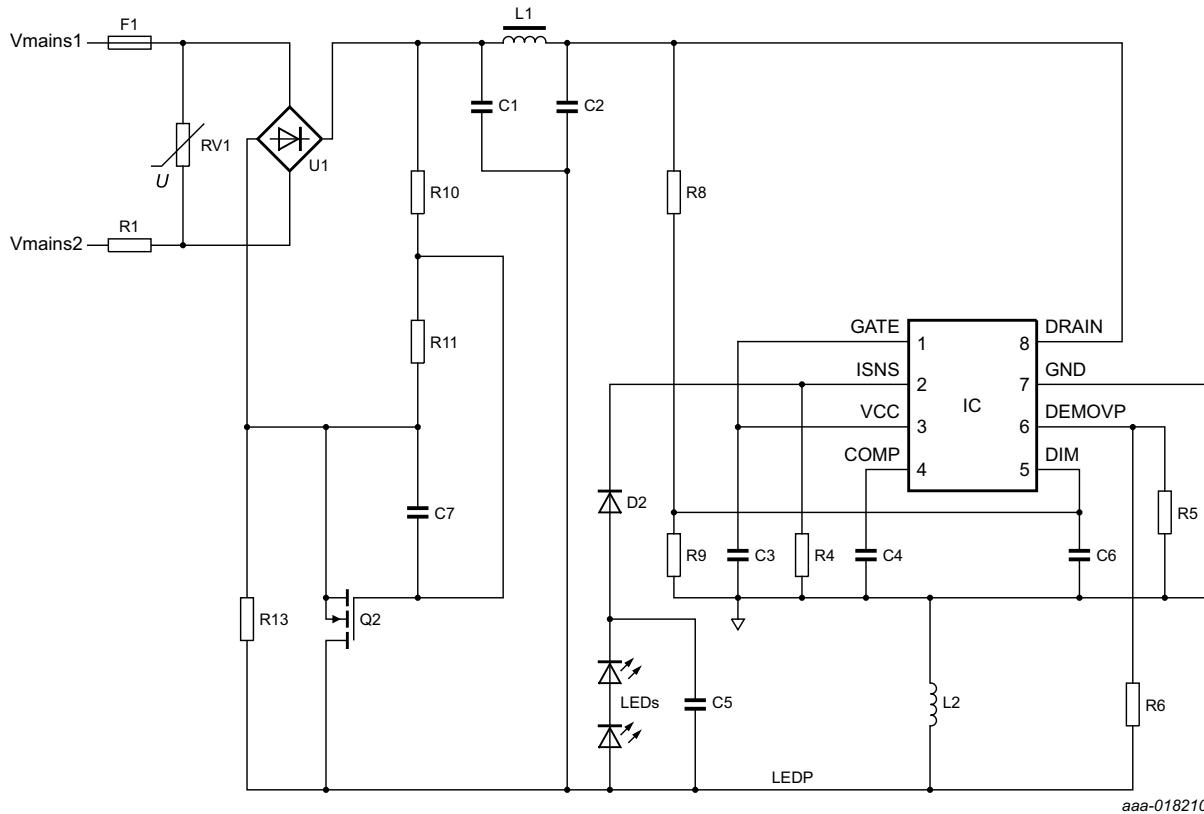
**Table 6. Characteristics ...continued**

$T_{amb} = 25 \text{ }^{\circ}\text{C}$ ;  $V_{CC} = 15 \text{ V}$ ; all voltages are measured with respect to ground pin (pin 7); currents are positive when flowing into the IC; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Temperature protection</b>						
$T_{th(fold)}$	foldback threshold temperature		[5]	125	135	$^{\circ}\text{C}$
$T_{pl(IC)}$	IC protection level temperature			140	150	$^{\circ}\text{C}$
$T_{pl(IC)rst}$	reset IC protection level temperature			106	118	$^{\circ}\text{C}$

- [1] The start-up voltage and the clamp voltage are correlated.
- [2] Guaranteed by design.
- [3]  $t_{leb} = t_{on(min)} - t_d$ ;  $t_{on(min)}$  is only effective when OCP is triggered.
- [4] The value is based on extrapolated data.
- [5] The IC foldback and the IC protection level temperature are correlated.

## 12. Application information



**Fig 9.** SSL5257TE typical application diagram

## 13. Package outline

HSO8: plastic thermal enhanced small outline package;  
8 leads; body width 3.9 mm; exposed die pad

SOT786-3

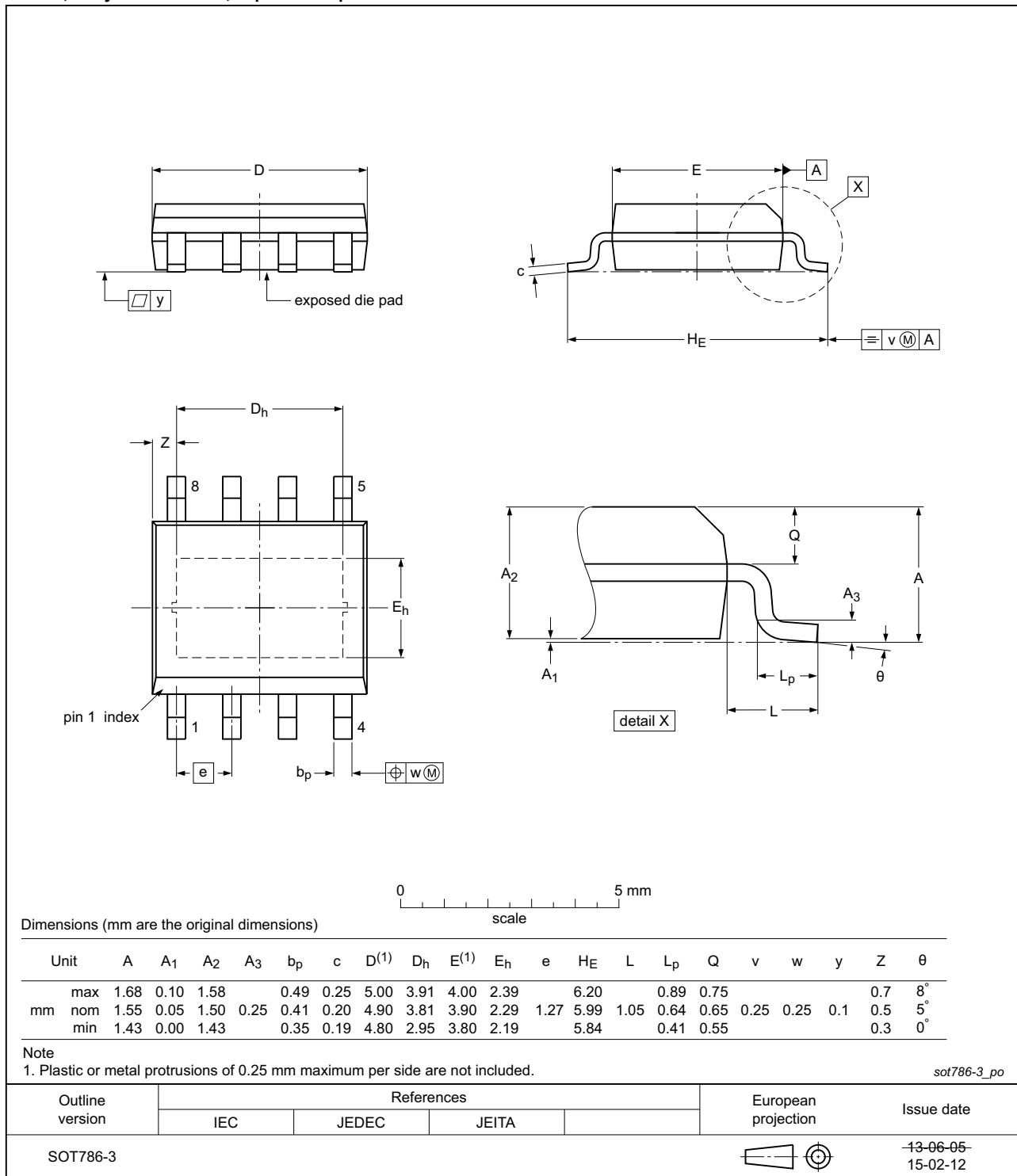


Fig 10. Package outline SOT786-3 (HSO8)

## 14. Revision history

**Table 7. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
SSL5257TE v.2	20150911	Product data sheet	-	SSL5257TE v.1
Modifications:	<ul style="list-style-type: none"><li>The data sheet status has changed from Preliminary to Product.</li><li><a href="#">Section 2 “Features and benefits”</a> has been updated.</li><li><a href="#">Section 4 “Quick reference data”</a> has been updated.</li><li><a href="#">Figure 1 “SSL5257TE block diagram”</a> has been updated.</li><li><a href="#">Table 6 “Characteristics”</a> has been updated.</li></ul>			
SSL5257TE v.1	20150721	Preliminary data sheet	-	-

## 15. Legal information

### 15.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

### 15.2 Definitions

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